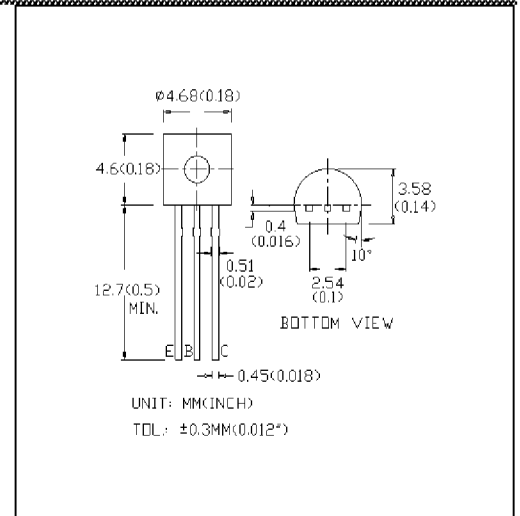


DESCRIPTION

BC450 is PNP silicon planar transistor designed for use as high voltage driver and output transistor. Particularly suitable as power darlington drivers.



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	100V
Collector-Base Voltage	V _{CB0}	100V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current Continuous	I _C	300mA
Total Power Dissipation @ Ta < 25°C	P _{tot}	625mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LV _{CEO} *	100		V	I _C = 1mA, I _B = 0
Collector-Base Breakdown Voltage	BV _{CB0}	100		V	I _C = 0.1mA, I _E = 0
Emitter-Base Breakdown Voltage	BV _{EB0}	4		V	I _E = 0.01mA, I _C = 0
Collector Cutoff Current	I _{CB0}		100	nA	V _{CB} = 60V, I _E = 0
D.C. Current Gain	HFE*	50	460		I _C = 2mA**, V _{CE} = 5V
		50			I _C = 10mA**, V _{CE} = 5V
		50			I _C = 100mA**, V _{CE} = 5V
Collector-Emitter Saturation Voltage	V _{CE(sat)} *		0.25	V	I _C = 100mA, I _B = 10mA
Base-Emitter Saturation Voltage	V _{BE(sat)} *	0.85	TYP.	V	I _C = 100mA, I _B = 10mA
Base-Emitter Voltage	V _{BE} *		1.2	V	I _C = 100mA, V _{CE} = 5V
Current Gain Bandwidth Product	f _T	100		MHz	I _C = 50mA, V _{CE} = 5V
Output Capacitance	C _{ob}	3	TYP.	pF	V _{CB} = 10V, f = 1MHz
Input Capacitance	C _{ib}	20	TYP.	pF	V _{EB} = 0.5V, f = 1MHz

* Pulse test : pulse width < 300μs, duty cycle < 1%.

HFE GROUPING :	Full range	Group A	Group B
@ I _C = 2mA V _{CE} = 5V	50-460	120-220	180-460
@ I _C = 10mA V _{CE} = 5V	50 min	100 min	160 min
@ I _C = 100mA V _{CE} = 5V	50 min	60 min	90 min